

Why GaN in Space?

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Packaged SEE Immune and Radiation Hardened enhancement mode gallium nitride (eGaN®) devices offer dramatically improved performance over the aging Rad Hard silicon MOSFET, enabling a new generation of power converters in space operating at higher frequencies, higher efficiencies, and greater power densities than ever achievable before. This presentation will show why GaN power transistors and ICs the best choice for power conversion application in space-based systems.